



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



**SCOPE: MONOLITHIC CMOS, ANALOG MULTIPLEXER**

<u>Device Type</u>	<u>Generic Number</u>	<u>SMD Number</u>
01	DG508AA(x)/883B	7705201

**Case Outline(s).** The case outlines shall be designated in Mil-Std-1835 and as follows:

<u>Outline Letter</u>	<u>Mil-Std-1835</u>	<u>Case Outline</u>	<u>Package Code</u>
MAXIM	SMD		
K	E	GDIP1-T16 or CDIP2-T16	16 LEAD CERDIP J16
L	X	CDFP4-16	16 LEAD FLATPACK F16
P	E	GDIP1-T16 or CDIP2-T16	16 LEAD Sidebrazed P16
Z	2	CQCC1-N20	20-Pin Ceramic LCC L20

**Absolute Maximum Ratings**

Voltage Referenced to V<sup>-</sup>

V <sup>+</sup> to V <sup>-</sup> .....	44V
V <sup>+</sup> to GND .....	+22V
V <sup>-</sup> to GND .....	-22V
Digital Inputs, VS or VD <u>1</u> /.....	(V <sup>-</sup> ) -3.0V to (V <sup>+</sup> )
Analog Inputs Voltage .....	(V <sup>-</sup> ) -2.0V to (V <sup>+</sup> ) +2V
Analog Input, Overvoltage Range .....	(V <sup>-</sup> ) -3.0V to (V <sup>+</sup> )

Lead Temperature (soldering, 10 seconds) ..... +300°C

Storage Temperature ..... -65°C to +150°C

Continuous Power Dissipation ..... T<sub>A</sub>=+70°C

16 lead FLATPACK (derate 6.1mW/°C above +70°C) ..... 485mW

16 lead CERDIP(derate 10.0mW/°C above +70°C) ..... 800mW

16 lead Side Braze(derate 10.5mW/°C above +70°C) ..... 842mW

20 lead LCC (derate 9.1mW/°C above +70°C) ..... 727mW

Junction Temperature T<sub>J</sub> ..... +150°C

Thermal Resistance, Junction to Case, Θ<sub>JC</sub>:

Case Outline 16 lead FLATPACK ..... 65°C/W

Case Outline 16 lead CERDIP..... 50°C/W

Case Outline 16 lead Side Braze..... 45°C/W

Case Outline 20 lead LCC ..... 20°C/W

Thermal Resistance, Junction to Ambient, Θ<sub>JA</sub>:

Case Outline 16 lead FLATPACK ..... 165°C/W

Case Outline 16 lead CERDIP..... 100°C/W

Case Outline 16 lead Side Braze..... 95°C/W

Case Outline 20 lead LCC ..... 110°C/W

**Recommended Operating Conditions.**

Ambient Operating Range (T<sub>A</sub>) ..... -55°C to +125°C

NOTE 1: Signals on S, D, IN exceeding V<sup>+</sup> or V<sup>-</sup> will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TABLE 1. ELECTRICAL TESTS**

TEST	Symbol	CONDITIONS	Group A Subgroup	Device type	Limits Min	Limits Max	Units
		-55 °C ≤T <sub>A</sub> ≤ +125°C V <sub>+</sub> =+15V, V <sub>-</sub> =-15V, GND=0V V <sub>AH</sub> =2.4V, V <sub>AL</sub> =0.8V, V <sub>EN</sub> =4.5V Unless otherwise specified					
<b>SWITCH</b>							
Input Leakage Current <u>2/</u>	I <sub>IH</sub>	Measure inputs sequentially, connect all unused inputs to GND	1,2,3	All		0.8	μA
Input Leakage Current <u>2/</u>	I <sub>IL</sub>	Measure inputs sequentially, connect all unused inputs to 5.0V	1,2,3	All		-0.8	μA
Switch ON Resistance	r <sub>DS(ON1)</sub>	I <sub>D</sub> =±1mA, V <sub>S</sub> =±10V	1,3 2	All		400 500	Ω
Switch ON Resistance	r <sub>DS(ON2)</sub>	V <sub>+</sub> =+10V, V <sub>-</sub> =±10V, I <sub>D</sub> =±1mA, V <sub>S</sub> =±7.5V	1,2,3	All		1000	Ω
Source-OFF Leakage Current	±I <sub>S(OFF)</sub>	V <sub>S</sub> =+/-10V, V <sub>EN</sub> =0.8V, All unused inputs=±10V	1,2,3	All	-50	50	nA
Drain-OFF Leakage Current	±I <sub>D(OFF)</sub>	V <sub>D</sub> =±10V, V <sub>EN</sub> =0.8V, All unused inputs=±10V	1,2,3	All	-250	250	nA
Drain-ON Leakage Current	±I <sub>D(ON)</sub>	V <sub>S</sub> =+/-10V, V <sub>D</sub> =-/+10V, All unused inputs=±10V	1,2,3	All	-250	250	nA
<b>INPUT</b>							
Standby Positive Supply Current	+I <sub>SBY</sub>	V <sub>A</sub> =0V, V <sub>EN</sub> =0V	1,2,3	All		3.5	mA
Standby Negative Supply Current	-I <sub>SBY</sub>	V <sub>A</sub> =0V, V <sub>EN</sub> =0V	1,2,3	All	-3.5		mA
<b>SUPPLY</b>							
Positive Supply Current	I <sub>+</sub>	V <sub>EN</sub> =5V, V <sub>A</sub> =0V	1,2,3	All		12	mA
Negative Supply Current	I <sub>+</sub>	V <sub>EN</sub> =5V, V <sub>A</sub> =0V	1,2,3	All	-12		mA
<b>DYNAMIC</b>							
Capacitance: Address	C <sub>A</sub>	V <sup>+</sup> =V <sup>-</sup> =0V, f=1MHz, NOTE 3	4	All		10	pF
Capacitance: Output Switch	C <sub>OS</sub>	V <sup>+</sup> =V <sup>-</sup> =0V, f=1MHz, NOTE 3	4	All		45	pF
Capacitance: Input Switch	C <sub>IS</sub>	V <sup>+</sup> =V <sup>-</sup> =0V, f=1MHz, NOTE 3	4	All		10	pF
Charge Transfer Error	V <sub>CTE</sub>	V <sub>S</sub> =GND, V <sub>GEN</sub> =0V to 5V, f=500kHz, CL=100pF NOTE 3	4	All		10	mV
Single Channel Isolation	V <sub>ISO</sub>	V <sub>GEN</sub> =1Vp-p, f=200kHz NOTE 3	4	All	50		dB
Crosstalk Between Channels	V <sub>CT</sub>	V <sub>GEN</sub> =1Vp-p, f=200kHz NOTE 3	4	All	50		dB
Break Before Make Time Delay	t <sub>D</sub>	Figure 3	9	All	5.0		ns
Propagation Delay: Address Inputs to I/O Channels	t <sub>ON(A)</sub> t <sub>OFF(A)</sub>	Figure 1,2, R <sub>L</sub> =1kΩ, CL=100pF	9,11 10	All		1000 1500	ns
Enable to I/O	t <sub>ON(EN)</sub> t <sub>OFF(EN)</sub>	Figure1,2, R <sub>L</sub> =1kΩ, CL=100pF	9,11 10	All		1000 1500	ns

NOTE 2: Input Current of one input mode.

NOTE 3: Guaranteed, if not tested, to the limits specified.

**FIGURE 1: SWITCHING TIME TEST CIRCUIT:** See Commercial Data Sheet

**FIGURE 2: ENABLE TIME TEST CIRCUIT:** See Commercial Data Sheet

**FIGURE 3: BREAK-BEFORE-MAKE TEST CIRCUIT:** See Commercial Data Sheet

ORDERING INFORMATION:	SMD NUMBER	PACKAGE CODE
DG508AAK/883B	7705201EA	16 CERDIP
DG508AAL/883B	7705201XC	16 FLATPACK
DG508AAP/883B	7705201EC	16 SIDE BRAZE
DG508AAZ/883B	77052012C	20 LCC

**TRUTH TABLE**

**TERMINAL CONNECTION**

A2	A1	A0	EN	DG508A ON SWITCH	TERMINAL NUMBER	DG508A	DG508A
X	X	X	L	None		J16, P16 & F16	L20
L	L	L	H	1	1	A0	NC
L	L	H	H	2	2	EN	A0
L	H	L	H	3	3	V-	EN
L	H	H	H	4	4	IN1	V-
H	L	L	H	5	5	IN2	IN1
H	L	H	H	6	6	IN3	NC
H	H	L	H	7	7	IN4	IN2
H	H	H	H	8	8	OUT	IN3
					9	IN8	IN4
					10	IN7	OUT
					11	IN6	NC
					12	IN5	IN8
					13	V+	IN7
					14	GND	IN6
					15	A2	IN5
					16	A1	NC
					17		V+
					18		GND
					19		A2
					20		A1

## QUALITY ASSURANCE

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
  1. Test condition A, B, C, D.
  2. TA = +125°C, minimum.
  3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

**TABLE 2. ELECTRICAL TEST REQUIREMENTS**

Mil-Std-883 Test Requirements	Subgroups per Method 5005, Table 1
Interim Electric Parameters Method 5004	1
Final Electrical Parameters Method 5005	1*, 2, 3, 4**
Group A Test Requirements Method 5005	1, 2, 3, 4**, 9, 10, 11***
Group C and D End-Point Electrical Parameters Method 5005	1

\* PDA applies to Subgroup 1 only.

\*\* Subgroup 4 (capacitance measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance.

\*\*\* Subgroups 10 and 11, if not tested, shall be guaranteed to the specified limits in Table 1.